

19. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in claim 14, wherein the ferroelectric gate field-effect transistor comprises a single ferroelectric gate field-effect transistor per pixel.

20. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in any one of claims 8-11 and 15, wherein the ferroelectric gate field-effect transistor comprises a single ferroelectric gate field-effect transistor per pixel.

21. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in claim 16, wherein the ferroelectric gate field-effect transistor comprises a single ferroelectric gate field-effect transistor per pixel.

C1  
CMT  
22. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in any one of claims 2-6 and 12, wherein the ferroelectric gate field-effect transistor consists of a single type of semiconductor selected from one of an n-type and a p-type semiconductor.

23. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in claim 13, wherein the ferroelectric gate field-effect transistor consists of a single type of semiconductor selected from one of an n-type and a p-type semiconductor.

24. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in claim 14, wherein the ferroelectric gate field-effect transistor consists of a single type of semiconductor selected from one of an n-type and a p-type semiconductor.

25. (Amended) The two-dimensional active-matrix type light-emitting device as set forth in any one of claims 8-11 and 15, wherein the ferroelectric gate field-effect transistor

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consists of a single type of semiconductor selected from one of an n-type and a p-type semiconductor.

*C1*  
*Amended*  
<sup>27</sup>~~26~~ (Amended) The two-dimensional active-matrix type light-emitting device as set  
<sup>25</sup>  
forth in claim ~~16~~, wherein the ferroelectric gate field-effect transistor consists of a single type of  
semiconductor selected from one of an n-type and a p-type semiconductor.

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